

Supplementary material

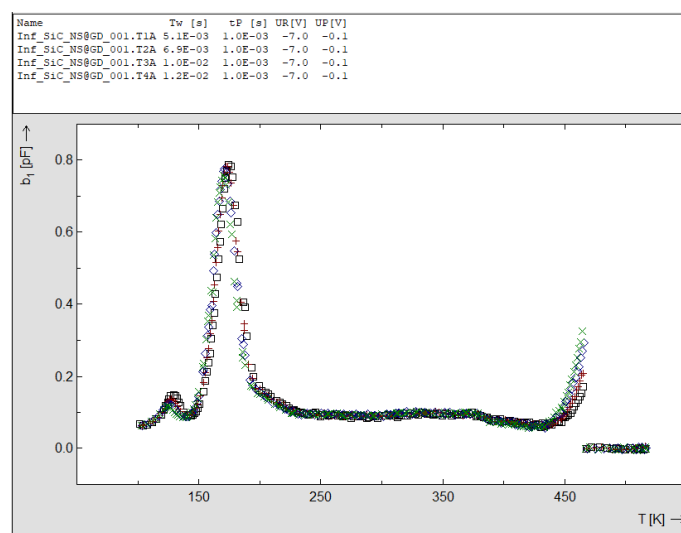
Charge Trap States of SiC Power TrenchMOS Transistor under Repetitive UIS Stress

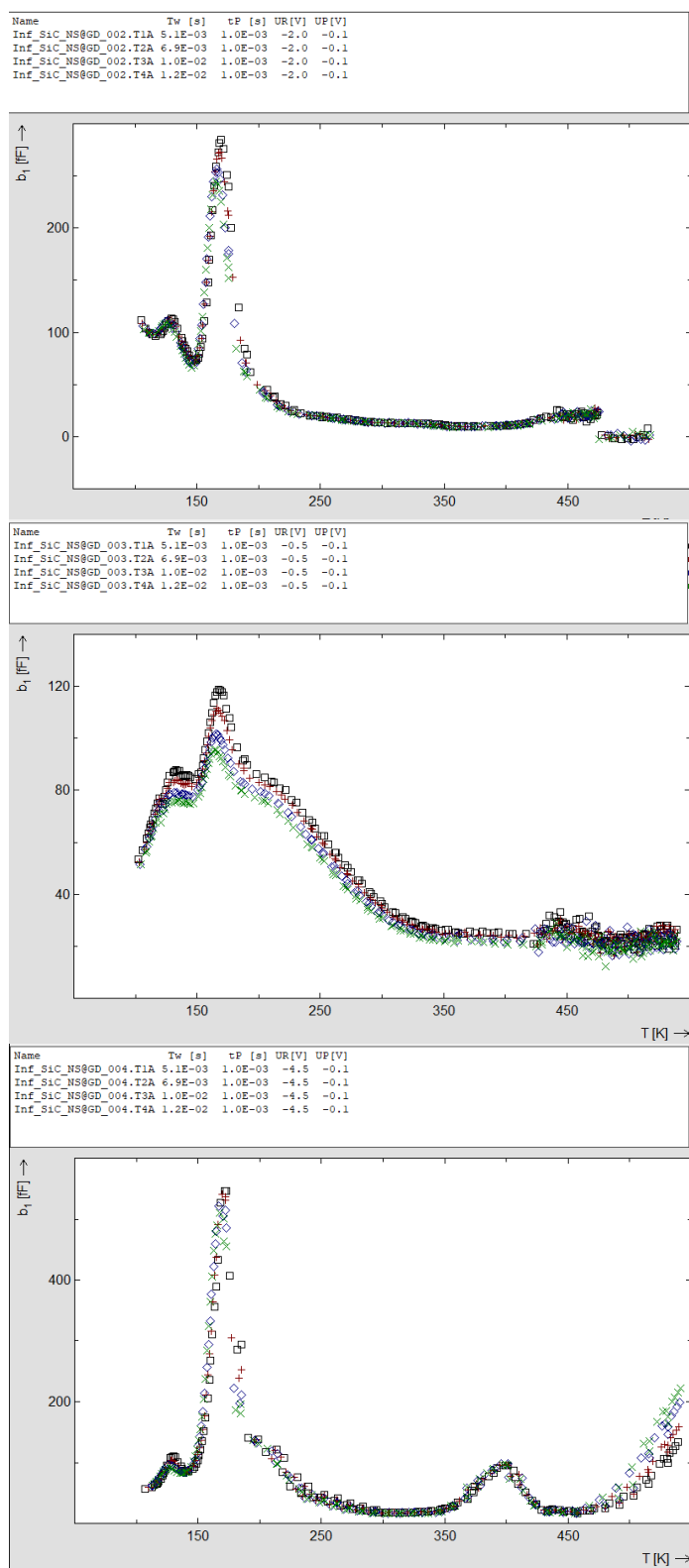
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Lubica Stuchlikova ¹ and Martin Weis ¹

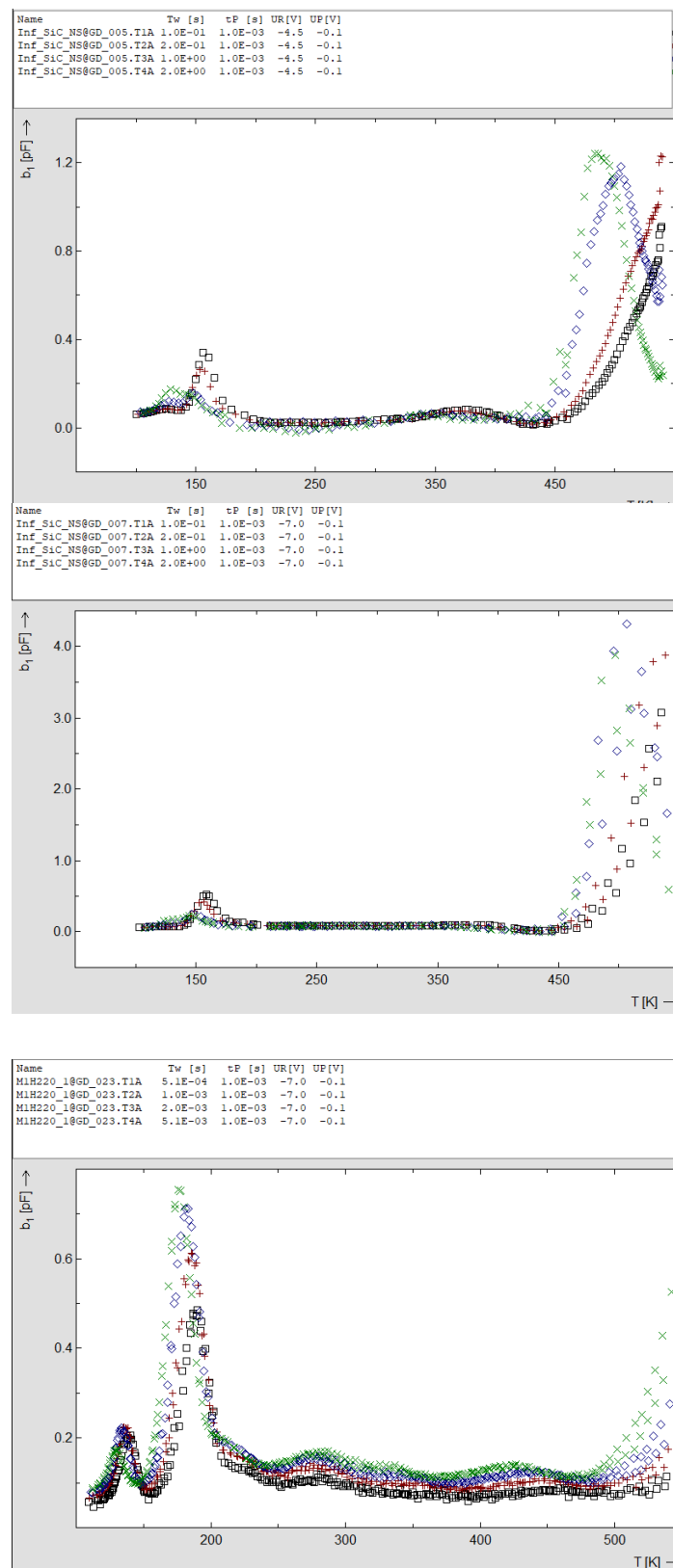
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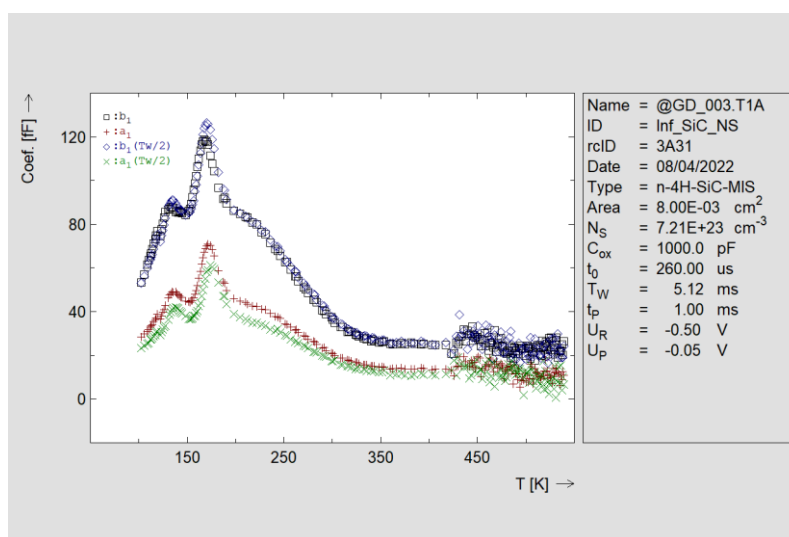
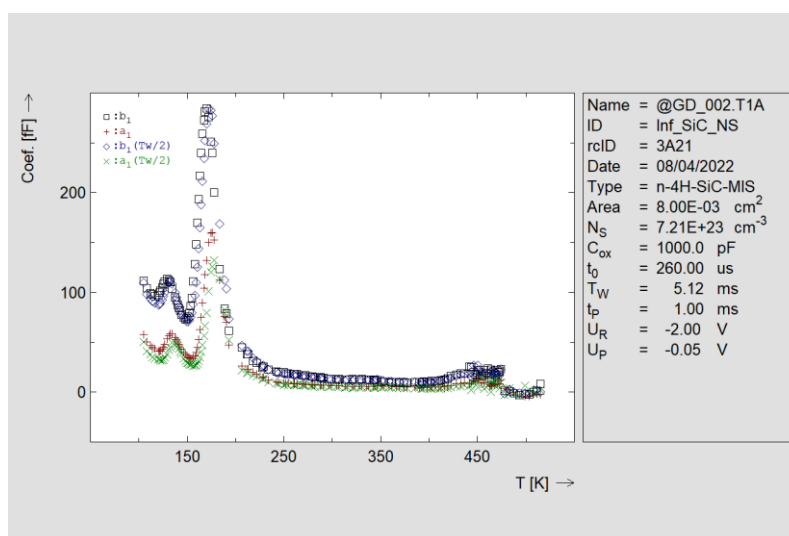
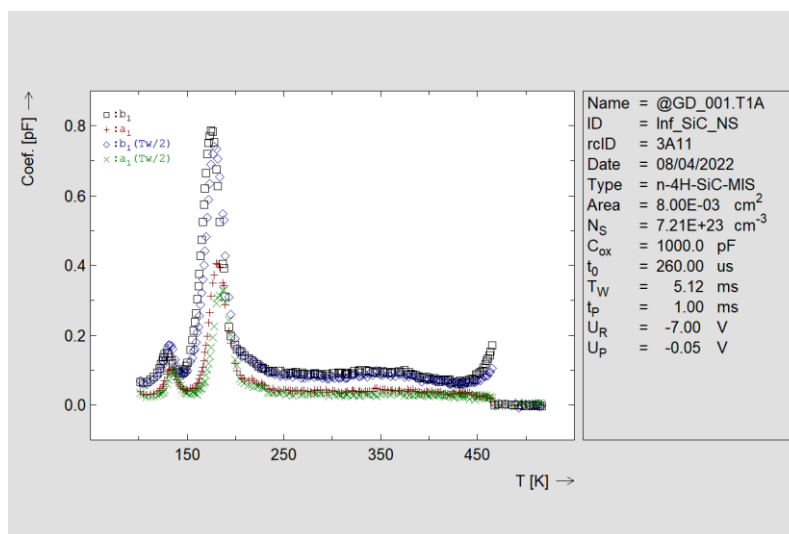
² NanoDesign, s.r.o, Drotárska 19a, 811 04 Bratislava, Slovakia

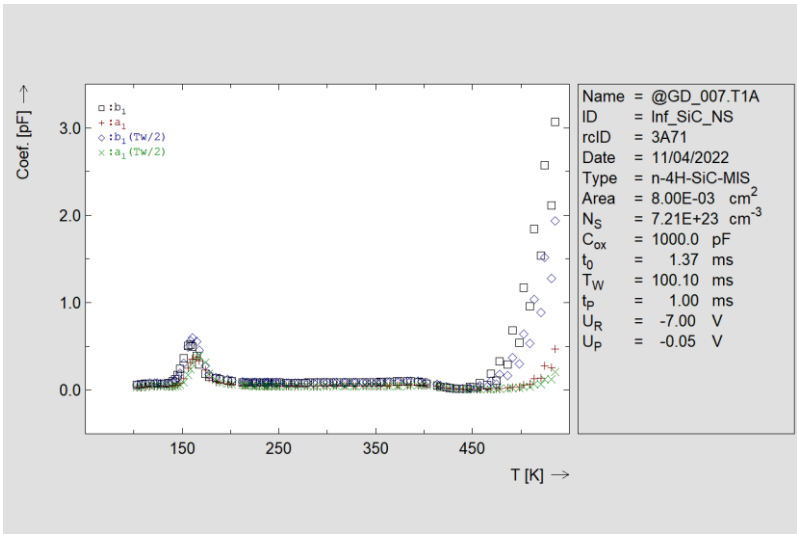
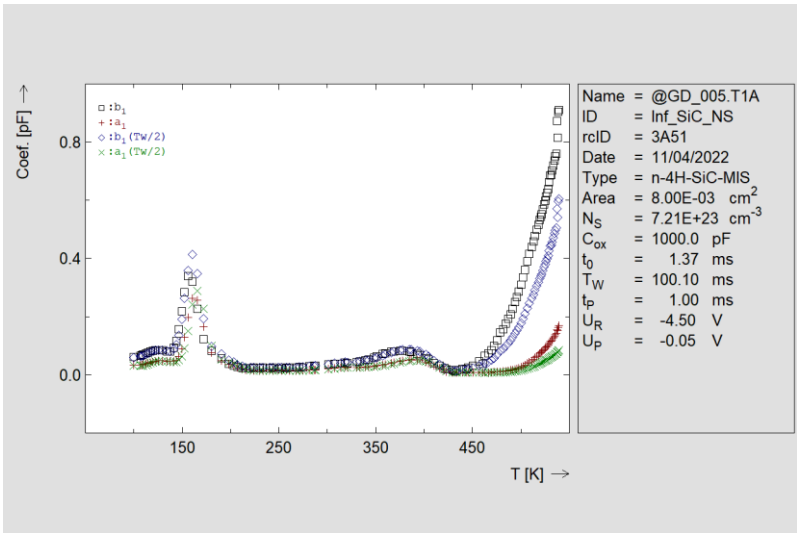
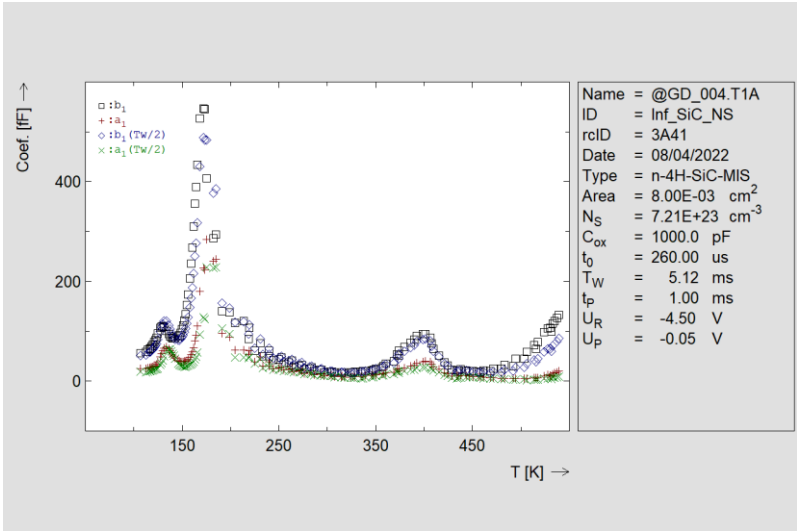
* Correspondence: juraj.marek@stuba.sk

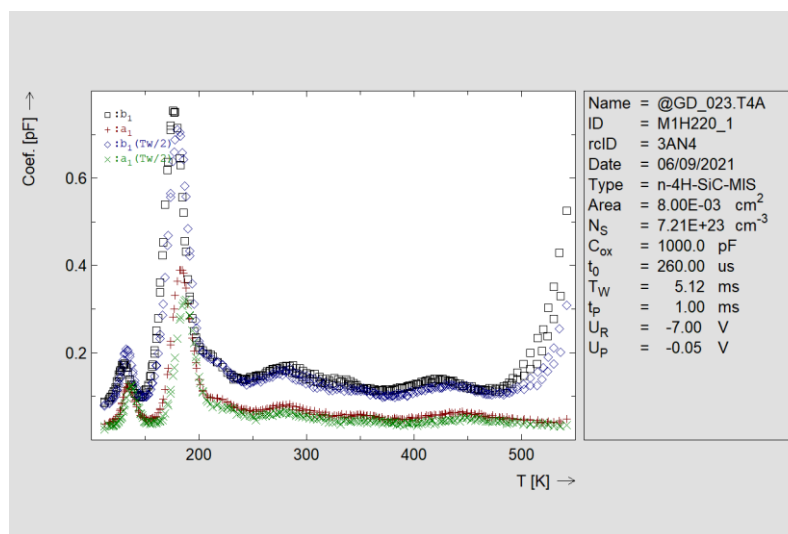




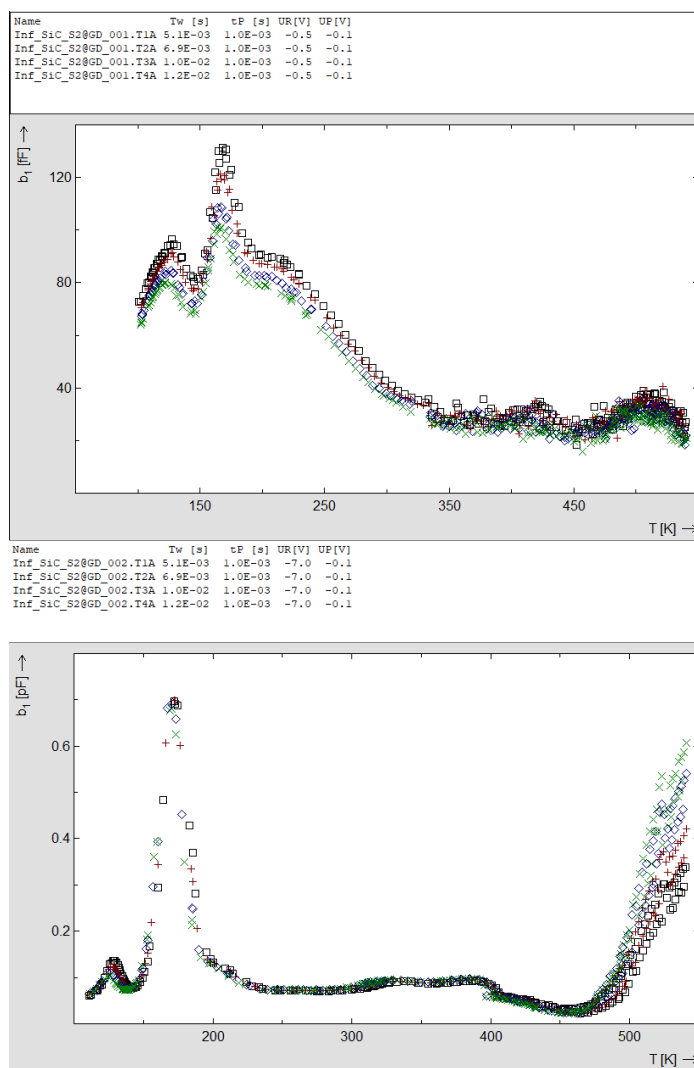


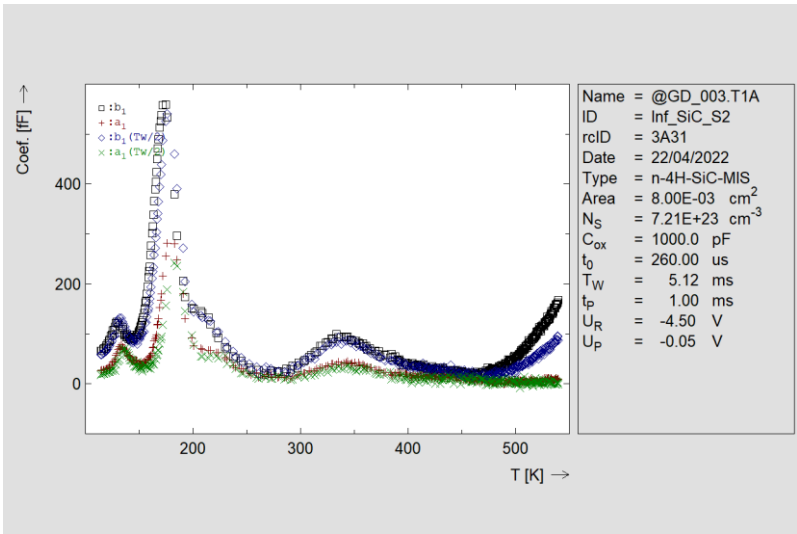
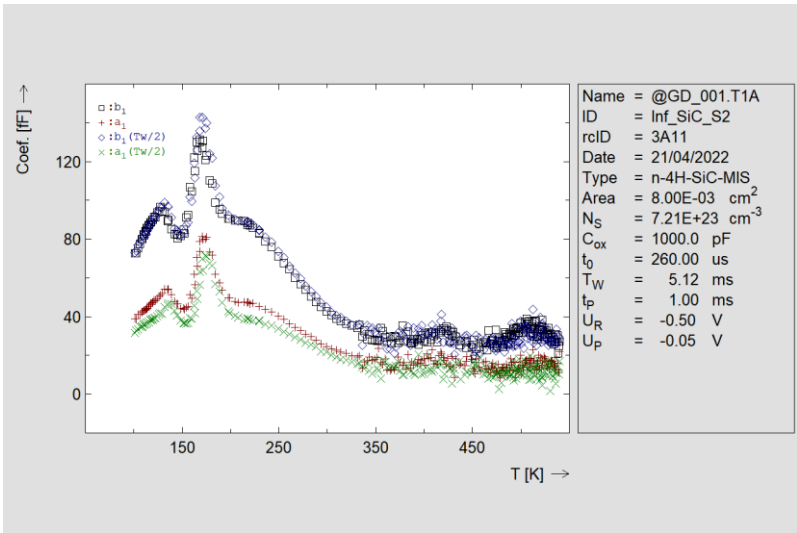
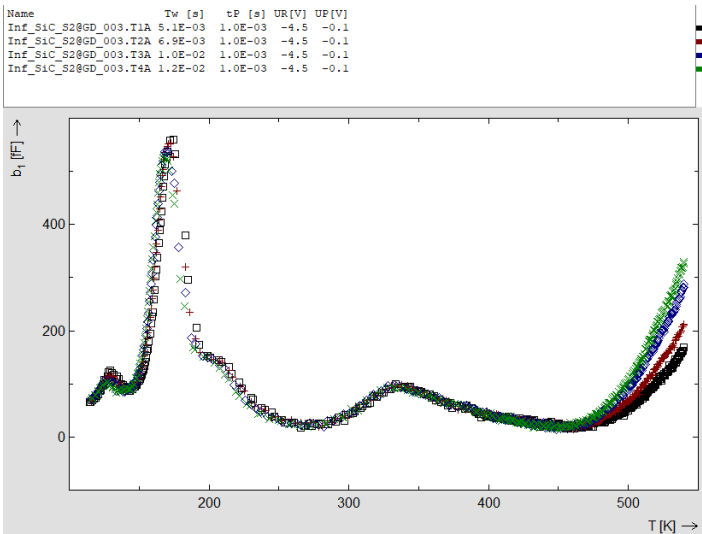


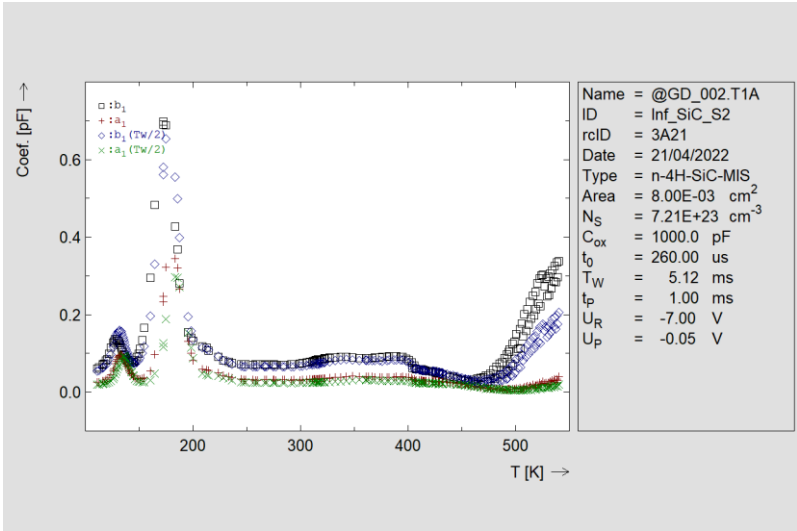




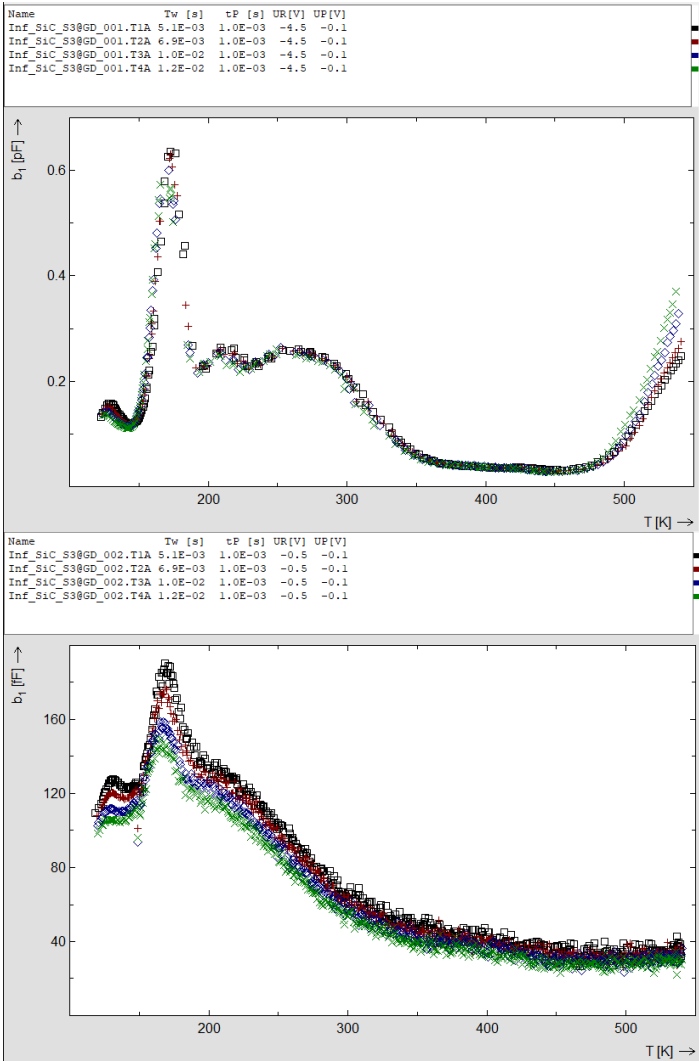
Measurements on virgin samples

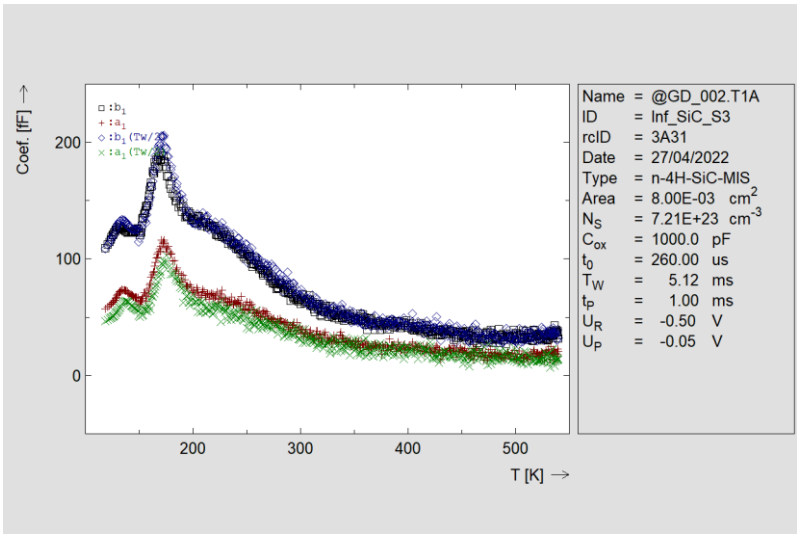
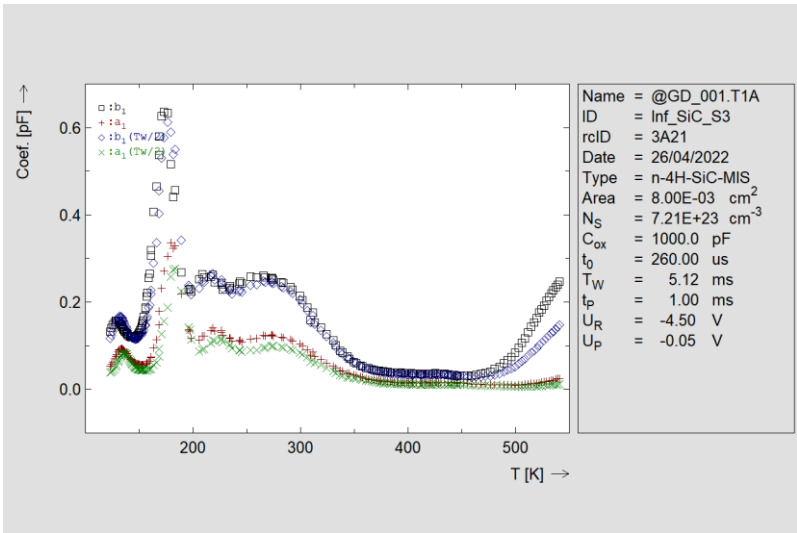
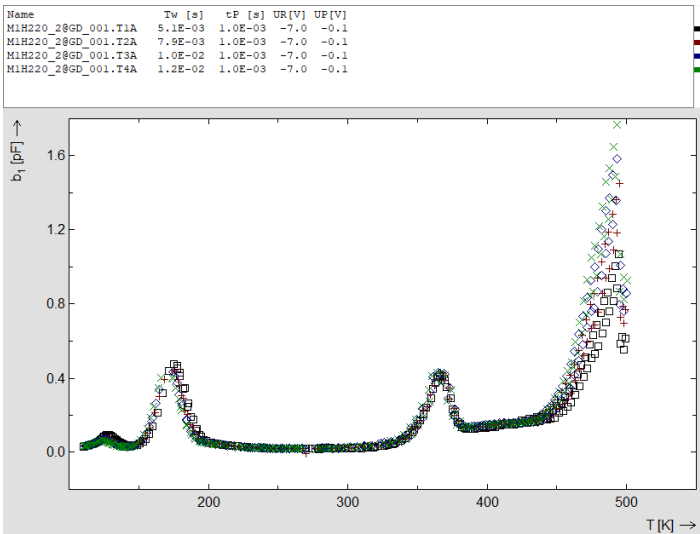


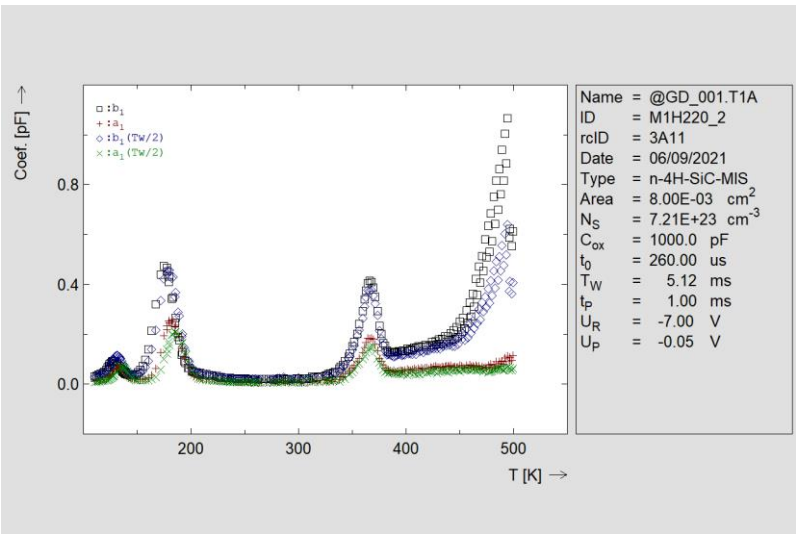




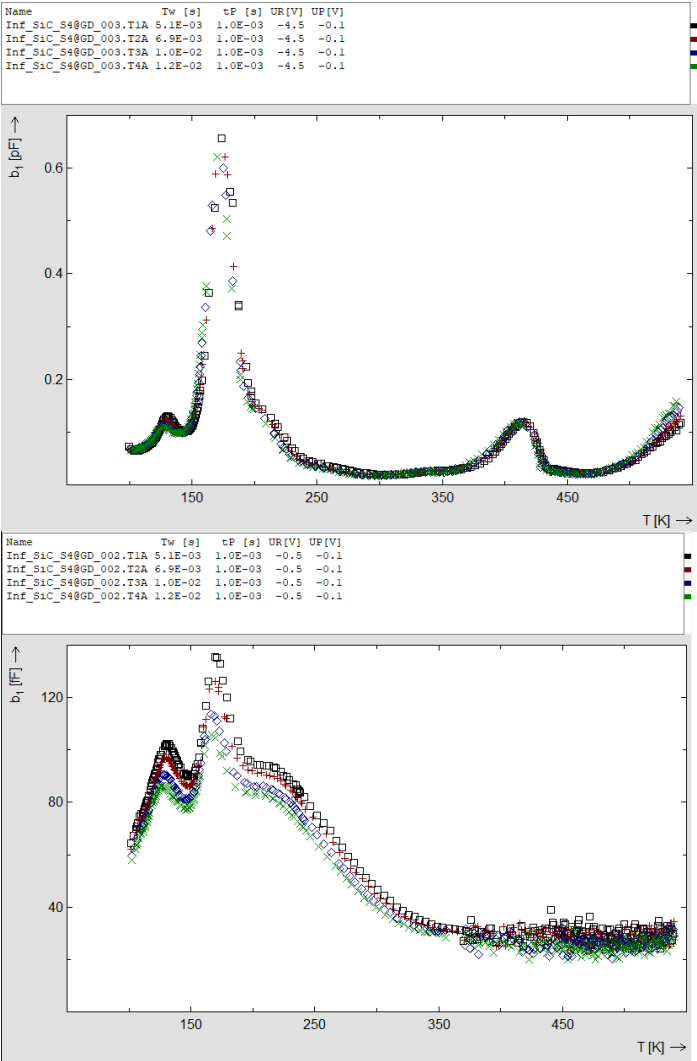
Measurements after 1 h of UISstress

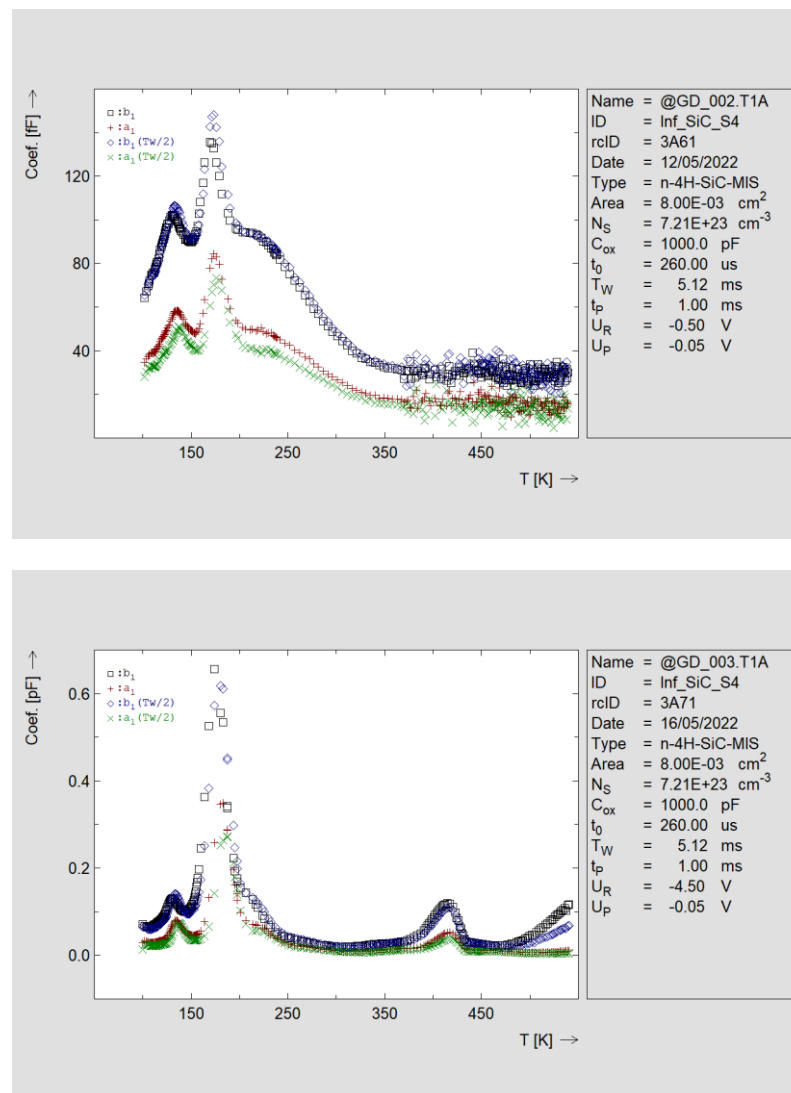






Measurements after 24 h of UIS stress





Static stress

Figure S1. Deep-level transient spectroscopy data.